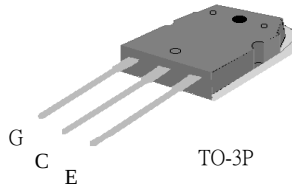


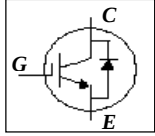


Features

- ▼ High Speed Switching
- ▼ Low Saturation Voltage
 $V_{CE(sat)}=3.0V@I_C=30A$
- ▼ CO-PAK, IGBT With FRD
- ▼ RoHS Compliant



V_{CES}	1200V
I_C	30A



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GE}	Gate-Emitter Voltage	± 30	V
$I_C@T_C=25^\circ C$	Continuous Collector Current	60	A
$I_C@T_C=100^\circ C$	Continuous Collector Current	30	A
I_{CM}	Pulsed Collector Current ¹	120	A
$I_F@T_C=25^\circ C$	Diode Forward Current	20	A
$I_F@T_C=100^\circ C$	Diode Forward Current	10	A
I_{FM}	Diode Pulse Forward Current	40	A
$P_D@T_C=25^\circ C$	Maximum Power Dissipation	208	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
T_L	Maximum Lead Temp. for Soldering Purposes , 1/8" from case for 5 seconds .	300	$^\circ C$

Notes:

1. Pulse width limited by max . junction temperature .

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c(IGBT)	Thermal Resistance Junction-Case	0.6	$^\circ C/W$
Rthj-c(Diode)	Thermal Resistance Junction-Case	1.5	$^\circ C/W$
Rthj-a	Thermal Resistance Junction-Ambient	40	$^\circ C/W$

Electrical Characteristics@ $T_J=25^\circ C$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I_{GES}	Gate-to-Emitter Leakage Current	$V_{GE}=\pm 30V, V_{CE}=0V$	-	-	± 500	nA
I_{CES}	Collector-Emitter Leakage Current	$V_{CE}=1200V, V_{GE}=0V$	-	-	1	mA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$V_{GE}=15V, I_C=30A$	-	3	3.6	V
		$V_{GE}=15V, I_C=60A$	-	3.8	-	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{CE}=V_{GE}, I_C=250uA$	3	-	7	V
Q_g	Total Gate Charge	$I_C=30A$	-	63	100	nC
Q_{ge}	Gate-Emitter Charge	$V_{CC}=500V$	-	12	-	nC
Q_{gc}	Gate-Collector Charge	$V_{GE}=15V$	-	32	-	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{CC}=600V, I_C=30A, V_{GE}=15V, R_G=5\Omega$	-	40	-	ns
t_r	Rise Time		-	45	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	125	-	ns
t_f	Fall Time		-	430	860	ns
E_{on}	Turn-On Switching Loss		-	1.3	-	mJ
E_{off}	Turn-Off Switching Loss		-	3.1	-	mJ
C_{ies}	Input Capacitance	$V_{GE}=0V$	-	1400	2240	pF
C_{oes}	Output Capacitance	$V_{CE}=30V$	-	120	-	pF
C_{res}	Reverse Transfer Capacitance	$f=1.0MHz$	-	15	-	pF

Electrical Characteristics of Diode@ $T_J=25^\circ C$ (unless otherwise specified)

V_F	Forward Voltage	$I_F=10A$	-	1.7	2.5	V
V_F	Forward Voltage	$I_F=20A$	-	2.1	2.9	V
t_{rr}	Reverse Recovery Time	$I_F=10A$	-	140	-	ns
Q_{rr}	Reverse Recovery Charge	$di/dt = 100 A/\mu s$	-	0.8	-	uC

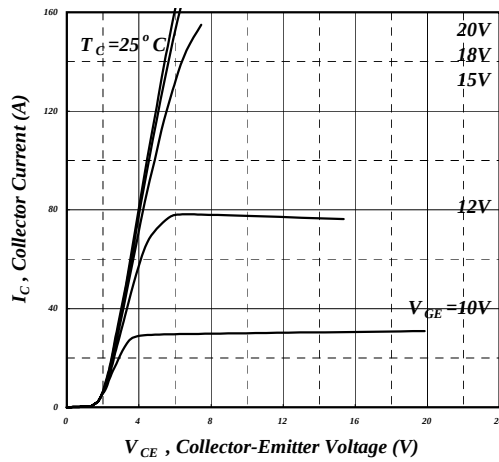


Fig 1. Typical Output Characteristics

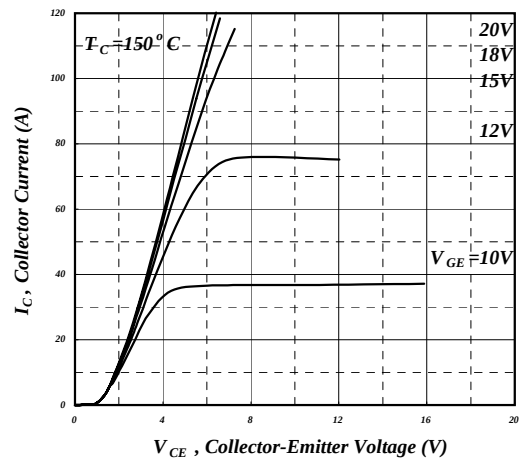


Fig 2. Typical Output Characteristics

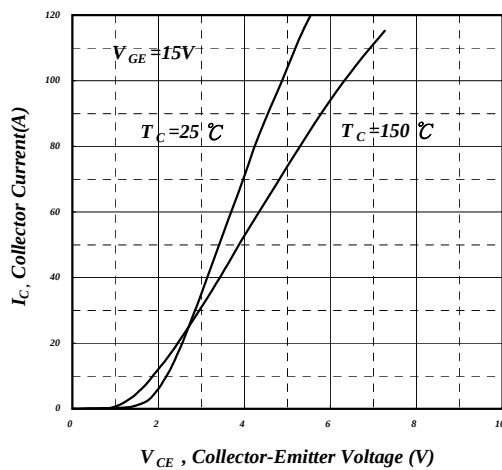


Fig 3. Typical Saturation Voltage Characteristics

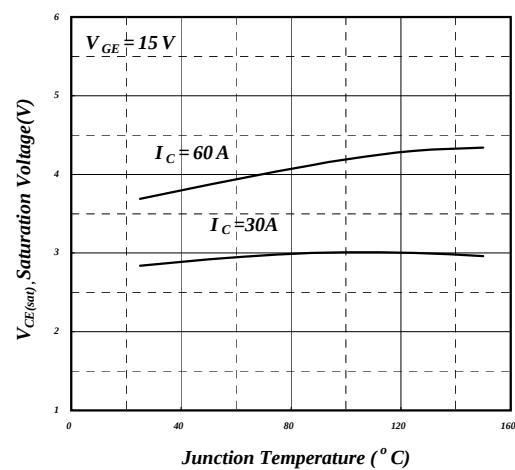


Fig 4. Typical Collector- Emitter Voltage v.s. Junction Temperature

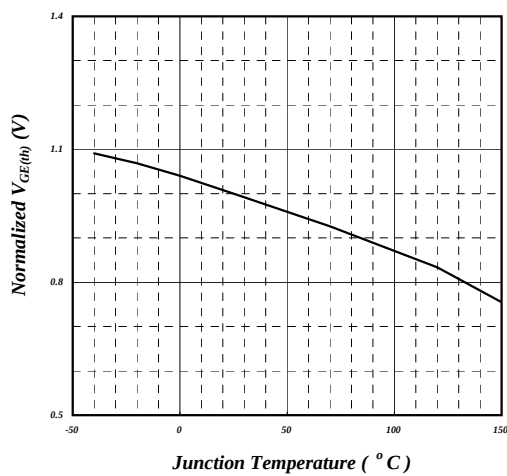


Fig 5. Gate Threshold Voltage v.s. Junction Temperature

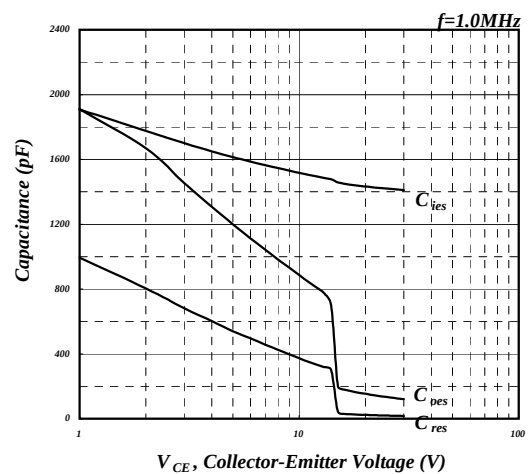


Fig 6. Typical Capacitance Characteristics

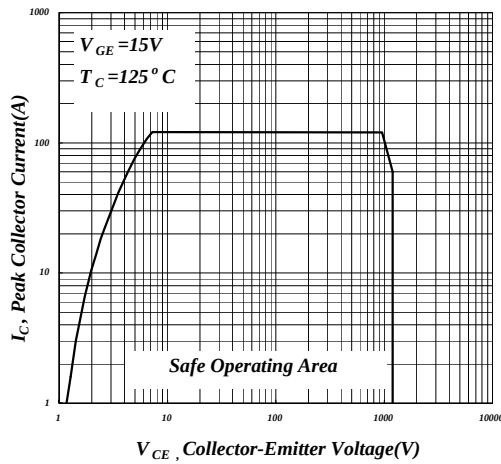


Fig 7. Turn-off SOA

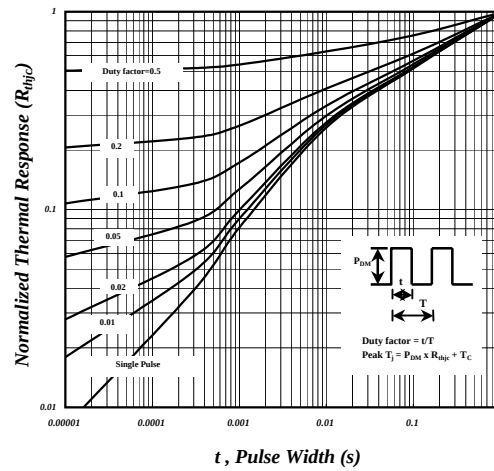


Fig 8. Effective Transient Thermal Impedance

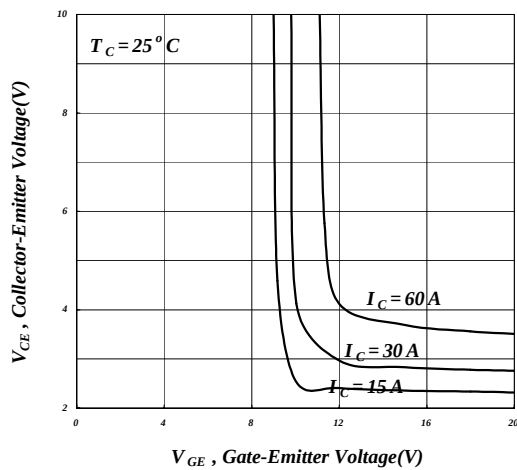


Fig 9. Saturation Voltage vs. V_{GE}

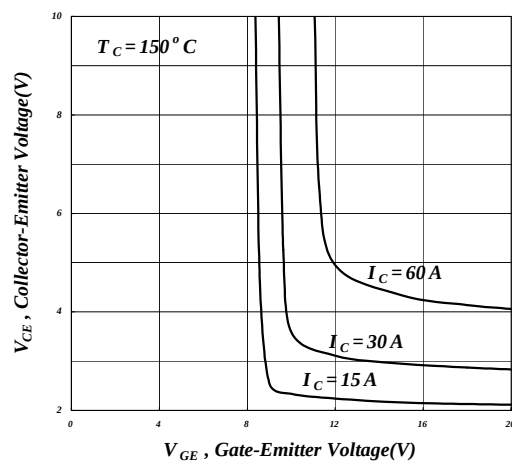


Fig 10. Saturation Voltage vs. V_{GE}

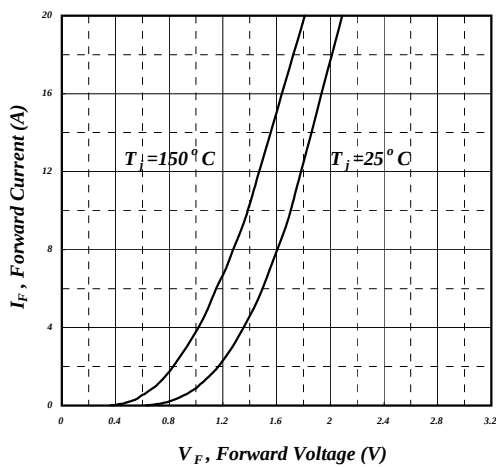


Fig11. Forward Characteristic of Diode

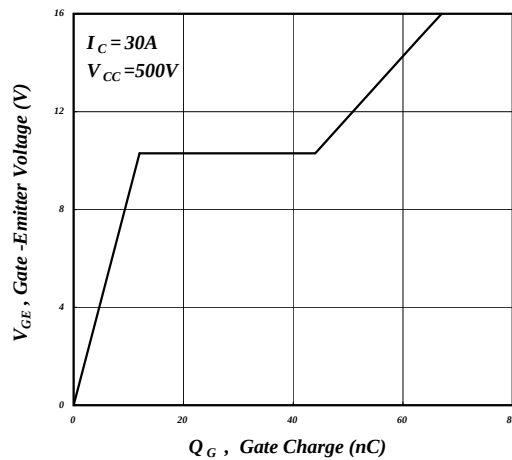


Fig 12. Gate Charge Characteristics